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Nobumitsu Honjou

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Ab initio study of band strength distribution for the D² Σ ⁺-A² Π transition of AlO and the effect of R dependence of the electronic transition moment on the distribution

by Nobumitsu Honjou

Oita University, 700 Dannoharu, Oita 870-1192, Japan

Abstract: The band strength distribution for the D² Σ ⁺ ν' -A² Π ν'' electronic transition of AIO, and the effect of R dependence of the electronic transition moment on the distribution, are studied based on the ab initio band strengths and the Franck-Condon factors (FCFs) for bands with vibrational quantum numbers $\nu = 0.18$ and $\nu = 0.18$. The band strength distribution exhibits a Condon parabola of the bands involving v=0-9 and 11 of all the inner-well levels of the $D^2\Sigma^+$ double potential well. Five unobserved bands calculated among the ten largest band strength bands are found to involve the ν' levels near the D² Σ^+ potential barrier top. The effect of the R dependence is examined for the FCF maximum bands in the ν progressions for $\nu=0.9$ and 11-18 (excluding $\nu=10$ of the D² Σ + outer-well level) by using the ratio of the band strength to the FCF, both relative to the 0-0 band. Large (Small) ratios of value 1.276-1.559 (0.619-0.841) are found for ratio>1 (ratio<1) bands with $\nu = 8$, 9 and 11-18. An analysis using a model of transition matrix element shows that the difference between (1) the electronic transition moment in the region represented by the R-centroid for each large ratio band and (2) that for the 0-0 band makes the greatest contribution to the ratio. The R-centroids do not properly represent the important R regions $(R<3.0 a_0)$ for the small ratio bands with $\nu=11-18$; a possible explanation is discussed. The results imply that the avoided crossings influence the band strength distribution. The Einstein A coefficients have been evaluated for the D-A bands with ν =0-9 and 11 and v''=0-18 from the calculated band strengths and transition energies.

Keywords: AlO; Ab initio; Band strength; Electronic transition moment; R-centroid; Einstein A coefficient;

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